Homework #5 Solutions

Problem 1:

For there to be between 20 mA and 100 mA of current flowing, the diode must be forward biased. The diode will take 2 V of $V_{digital}$, and the resistor will take the rest of $V_{digital}$.

The current flowing through the circuit will thus be

 $I_{diode} = (V_{digital} - 2 V)/R_{limit}$

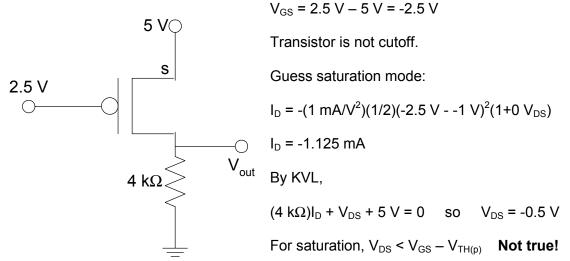
 R_{limit} must be small enough so that I_{diode} is at least 20 mA when V_{digital} is at its smallest, 4 V.

 $(4 V - 2 V)/R_{\text{limit}} \ge 20 \text{ mA}$ $R_{\text{limit}} \le 100 \Omega$

 R_{limit} must be big enough so that I_{diode} is less than 100 mA when $V_{digital}$ is at its biggest, 5 V.

 $(5 \text{ V} - 2 \text{ V})/\text{R}_{\text{limit}} \le 100 \text{ mA}$ $\text{R}_{\text{limit}} \ge 30 \Omega$

Problem 2:



So transistor must be in triode mode.

 $I_D = -(1 \text{ mA/V}^2)(-2.5 \text{ V} - -1 \text{ V} - (V_{DS}/2))(V_{DS})$

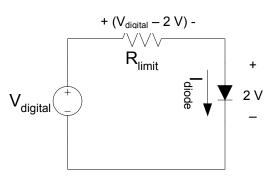
It's still true that $(4 \text{ k}\Omega)I_D + V_{DS} + 5 \text{ V} = 0$ so substitute to get

$$-(5 \text{ V} + \text{V}_{\text{DS}})/4 \text{ k}\Omega = -(1 \text{ mA/V}^2)(-2.5 \text{ V} - -1 \text{ V} - (\text{V}_{\text{DS}}/2))(\text{V}_{\text{DS}})$$

Solutions: $V_{DS} = \{-1 V, -2.5 V\}$

 V_{DS} = -2.5 V not possible for triode mode (need $V_{DS} > V_{GS} - V_{TH(p)}$) so V_{DS} = -1 V

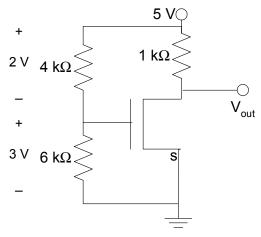
$$I_D = -(1 \text{ mA/V}^2)(-2.5 \text{ V} - -1 \text{ V} - (-1 \text{ V/2}))(-1 \text{ V}) = -1 \text{ mA}$$



 $V_{out} = V_{DS} + 5 V = 4 V$

(Typically, the numbers do not work out this nicely!)

Problem 3:



Notice that no current goes into or out of the gate. So the 4 k and 6 k transistors have the same current.

Voltage division or Ohm's law tells us that the 4 k resistor has 2 V and the 6 k resistor has 3 V as shown.

So V_{GS} = 3 V (over the 6 k resistor).

The transistor is not cutoff.

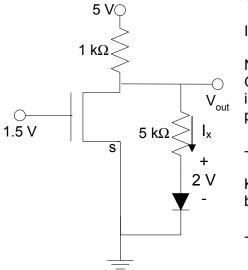
Guess saturation mode:

 $I_D = (1 \text{ mA/V}^2)(1/2)(3 \text{ V} -1 \text{ V})^2(1+0 \text{ V}_{DS})$ $I_D = 2 \text{ mA}$

By KVL, $(1 \text{ k}\Omega)I_D + V_{DS} - 5 \text{ V} = 0$ so $V_{DS} = 3 \text{ V}$

For saturation, $V_{DS} > V_{GS} - V_{TH(n)}$ Yes! Saturation was the right guess. $V_{out} = V_{DS} = 3 V$

Problem 4:



V_{GS} = 1.5 V Transistor is not cutoff. Guess saturation:

 $I_D = (1 \text{ mA/V}^2)(1/2)(1.5 \text{ V} -1 \text{ V})^2(1+0 \text{ V}_{DS})$ $I_D = 125 \,\mu\text{A}$

Now we must find V_{DS} . The only way to do this is by KVL. Guess that the diode is forward biased (small Vin means big Vout for our inverter). For large-signal model, this means diode has V_F = 2 V and some positive current. Now starting KVL at ground and going clockwise,

 $-V_{DS} + 5 k\Omega I_x + 2 V = 0$ Need to find I_x .

KVL again, starting at ground, going up diode branch and 1k resistor branch, dropping back to ground over 5 V source:

- 2 V - 5 kW
$$I_x$$
 – 1 k Ω (I_x + 125 μ A) + 5 V = 0

 $V_{DS} = 5 k\Omega I_x + 2 V$ (by previous KVL) $V_{DS} = 4.395 V$

For saturation, $V_{DS} > V_{GS} - V_{TH(n)}$ Yes! Saturation was the right guess. $V_{out} = V_{DS} = 4.395 V$